

MSD1819A-RT1G, NSVMSD1819A-RT1G

General Purpose Amplifier Transistor

NPN Silicon Surface Mount

This NPN Silicon Epitaxial Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

Features

- High h_{FE} , 210–460
- Low $V_{CE(sat)}$, < 0.5 V
- Moisture Sensitivity Level 1
- ESD Protection:
 - ◆ Human Body Model > 4000 V
 - ◆ Machine Model > 400 V
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{(BR)CBO}$	60	Vdc
Collector-Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	7.0	Vdc
Collector Current – Continuous	I_C	100	mA _{dc}
Collector Current – Peak	$I_{C(P)}$	200	mA _{dc}

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 1)	P_D	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

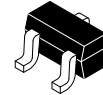
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

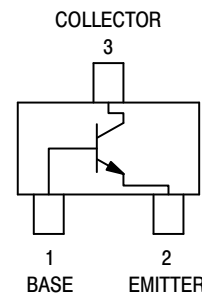


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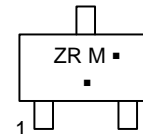
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SC-70 (SOT-323)
CASE 419
STYLE 3



MARKING DIAGRAM



ZR = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MSD1819A-RT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
NSVMSD1819A-RT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage ($I_C = 2.0 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	50	-	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \text{ } \mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	60	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \text{ } \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	7.0	-	Vdc
Collector-Base Cutoff Current ($V_{CB} = 20 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	-	0.1	μA
Collector-Emitter Cutoff Current ($V_{CE} = 10 \text{ Vdc}$, $I_B = 0$)	I_{CEO}	-	0.1	μA
DC Current Gain (Note 2) ($V_{CE} = 10 \text{ Vdc}$, $I_C = 2.0 \text{ mAdc}$) ($V_{CE} = 2.0 \text{ Vdc}$, $I_C = 100 \text{ mAdc}$)	h_{FE1} h_{FE2}	210 90	340 -	-
Collector-Emitter Saturation Voltage (Note 2) ($I_C = 100 \text{ mAdc}$, $I_B = 10 \text{ mAdc}$)	$V_{CE(sat)}$	-	0.5	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width $\leq 300 \text{ } \mu\text{s}$, D.C. $\leq 2\%$.

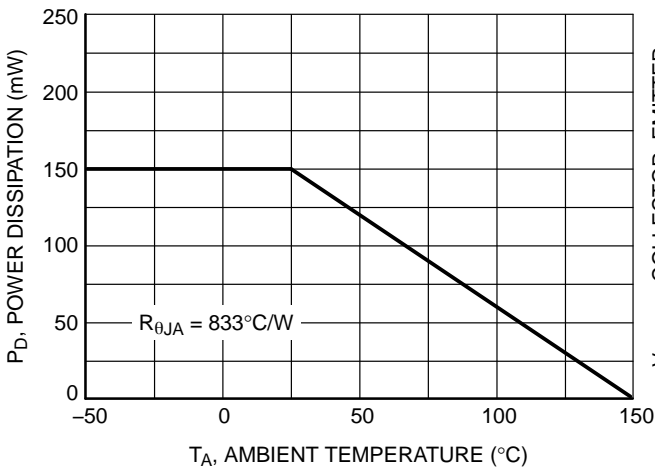


Figure 1. Derating Curve

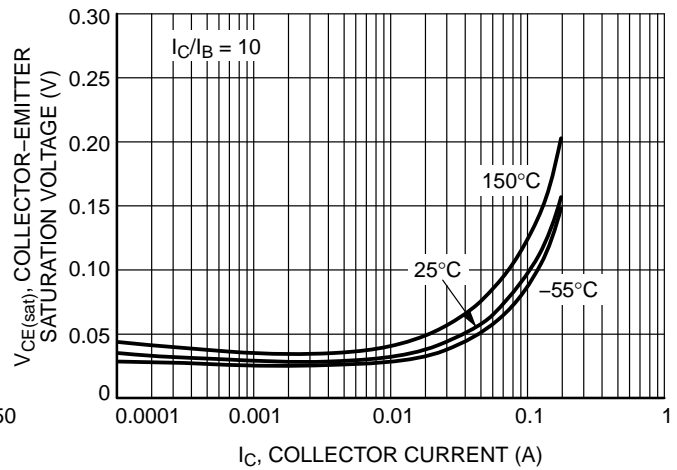


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

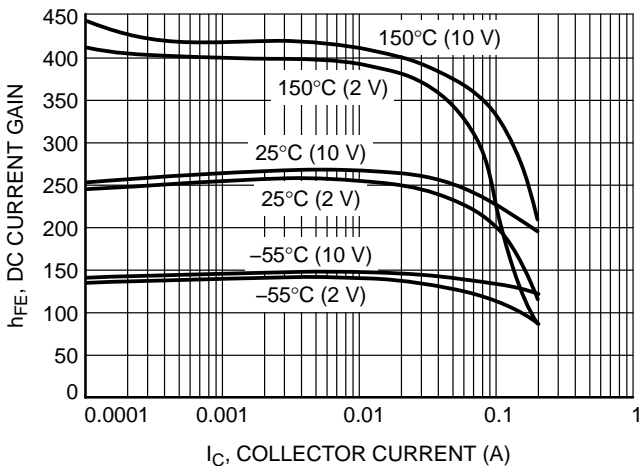


Figure 3. DC Current Gain vs. Collector Current

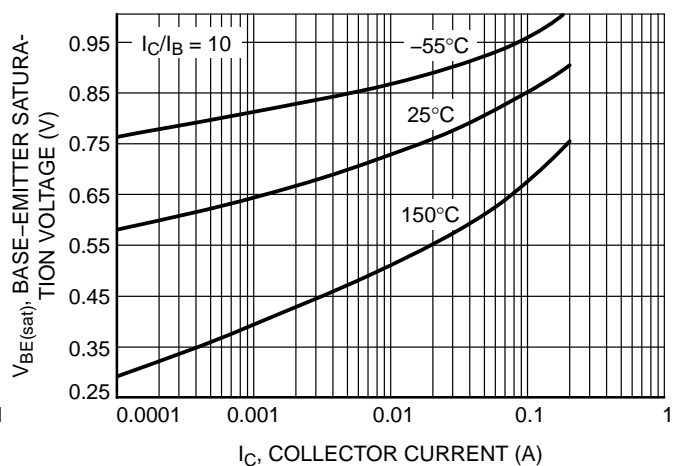


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

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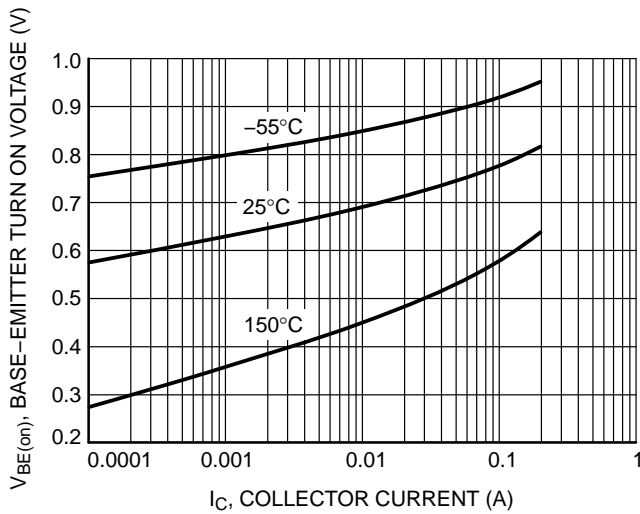


Figure 5. Base-Emitter Turn-On Voltage vs. Collector Current

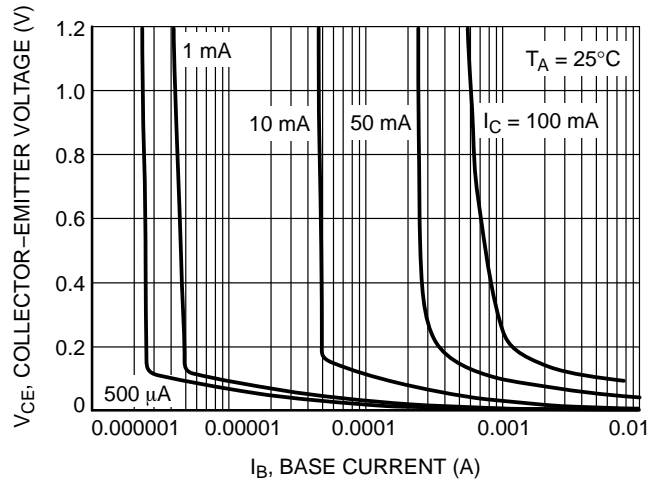


Figure 6. Collector Saturation Region

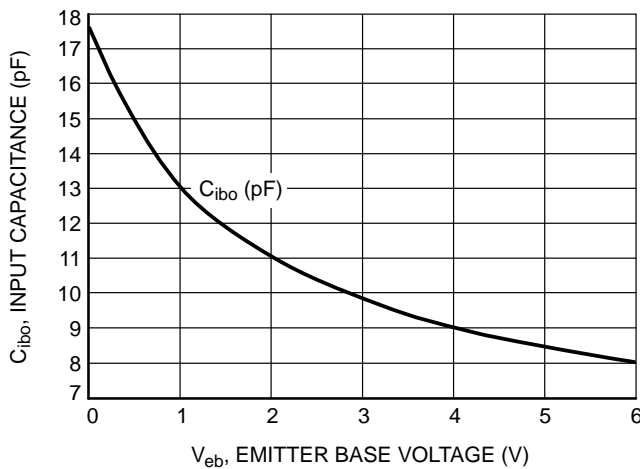


Figure 7. Input Capacitance

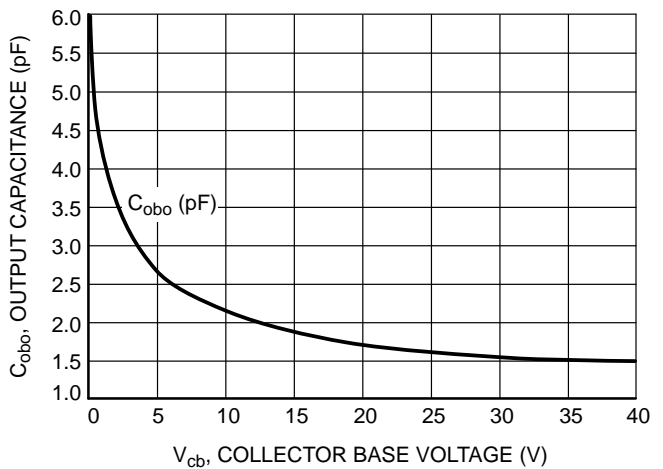


Figure 8. Output Capacitance

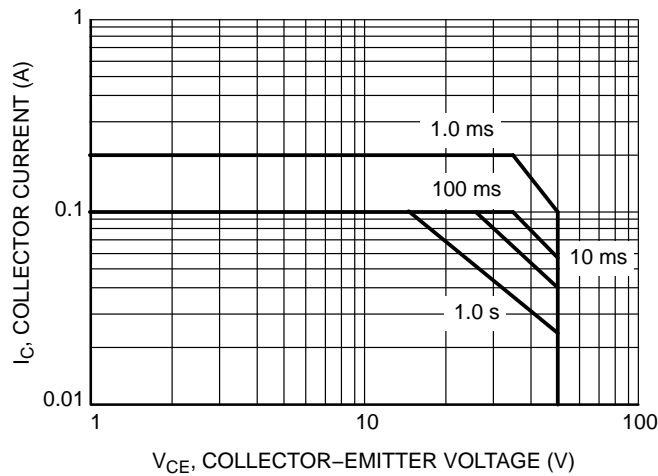
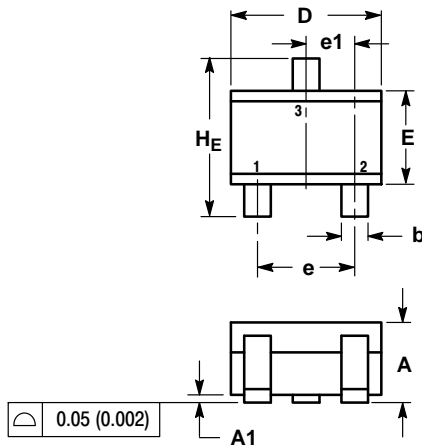


Figure 9. Safe Operating Area

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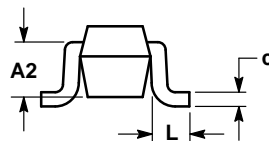
PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 ISSUE N



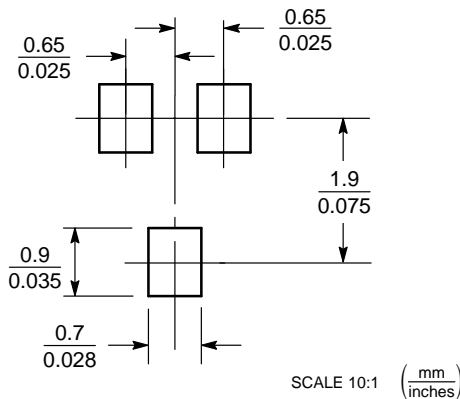
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



- STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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